



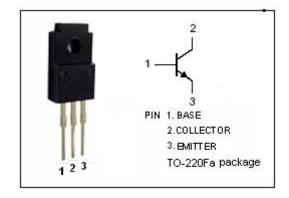
## isc Silicon NPN Power Transistor

### **DESCRIPTION**

- · Collector-Base Breakdown Voltage-
  - : V<sub>(BR)CBO</sub>= 800V(Min.)
- Wide Area of Safe Operation
- · High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

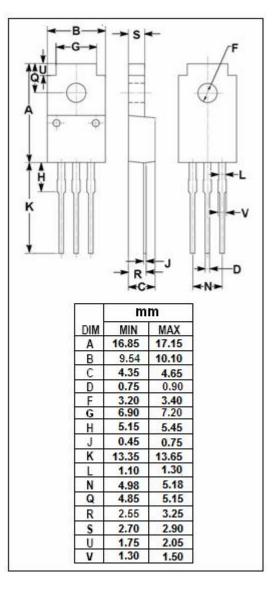
### **APPLICATIONS**

· Designed for high speed switching applications.



# ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>СВО</sub>	Collector-Base Voltage	800	V
V <sub>CES</sub>	Collector-Emitter Voltage	800	V
V <sub>CEO</sub>	Collector-Emitter Voltage	500	V
V <sub>EBO</sub>	Emitter-Base Voltage	8	V
Ic	Collector Current-Continuous	1.5	А
Ісм	Collector Current-Peak	3	А
I <sub>B</sub>	Base Current-Continuous	0.5	А
Pc	Collector Power Dissipation @T <sub>a</sub> =25℃	2	
	Collector Power Dissipation @T <sub>C</sub> =25°C	25	W
T <sub>j</sub>	Junction Temperature	150	$^{\circ}$ C
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$ C





### isc Silicon NPN Power Transistor

2SC3970

### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

TC-25 C unless otherwise specified								
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	500			V		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 0.6A; I <sub>B</sub> = 0.17A			1.0	V		
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I <sub>C</sub> = 0.6A; I <sub>B</sub> = 0.17A			1.5	V		
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 800V; I <sub>E</sub> = 0			100	μА		
ІЕВО	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			100	μА		
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	15					
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 0.6A; V <sub>CE</sub> = 5V	8					
f⊤	Current-Gain—Bandwidth Product	Ic= 0.1A; Vc== 10V; f= 1MHz		20		MHz		
Switching Times								
ton	Turn-on Time				1.0	μ <b>s</b>		
ts	Storage Time	I <sub>C</sub> = 0.6A; I <sub>B1</sub> = 0.17A; I <sub>B2</sub> = -0.34A; V <sub>CC</sub> = 200V			3.0	μ <b>S</b>		
tf	Fall Time				0.3	μS		

### **NOTICE:**

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